

Post doc or PhD position at Technion

Research field: semiconductor device: technology computer aided design of GaN heterostructure field effect transistor (HFET). Emphasis on trapping effects in RF and switching applications.

Required background: good understanding of semiconductor device physics, MATLAB, and optionally ADS and SENTAURUS or ATLAS software.

Collaborations: The research will be carried out as a joined project with the Ferdinand Braun Institute in Berlin, Cottbus University, and Stuttgart University.

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Starting date: Immediate